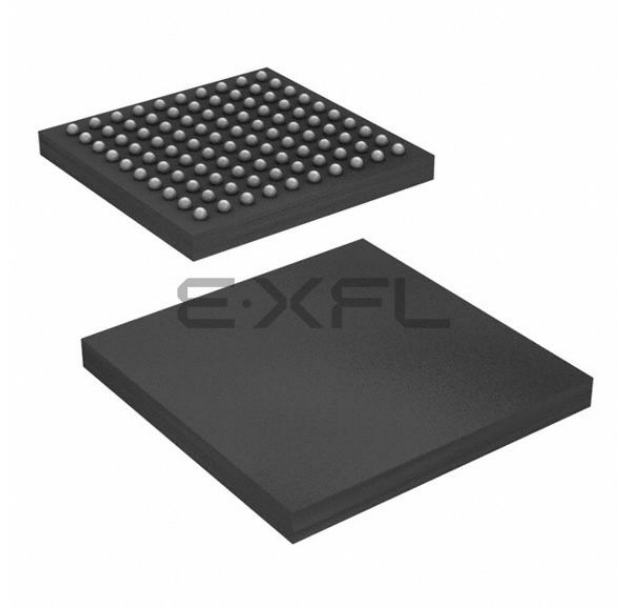

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	77
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	40K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 17x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA, WLCSP
Supplier Device Package	100-WLCSP (4.2x4.7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302vcy6tr

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F302xB/STM32F302xC microcontrollers.

This STM32F302xB/STM32F302xC datasheet should be read in conjunction with the STM32F302xx reference manual (RM0365). The reference manual is available from the STMicroelectronics website *www.st.com*.

For information on the Cortex®-M4 core with FPU, please refer to:

- **Cortex®-M4 with FPU Technical Reference Manual**, available from ARM website www.arm.com.
- **STM32F3xxx and STM32F4xxx Cortex®-M4 programming manual (PM0214)** available from our website *www.st.com*.

2 Description

The STM32F302xB/STM32F302xC family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core with FPU operating at a frequency of up to 72 MHz, and embedding a floating point unit (FPU), a memory protection unit (MPU) and an embedded trace macrocell (ETM). The family incorporates high-speed embedded memories (up to 256 Kbytes of Flash memory, up to 40 Kbytes of SRAM) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The devices offer up to two fast 12-bit ADCs (5 Msps), four comparators, two operational amplifiers, up to one DAC channel, a low-power RTC, up to five general-purpose 16-bit timers, one general-purpose 32-bit timer, and one timer dedicated to motor control. They also feature standard and advanced communication interfaces: up to two I^2Cs, up to three SPIs (two SPIs are with multiplexed full-duplex I2Ss), three USARTs, up to two UARTs, CAN and USB. To achieve audio class accuracy, the I2S peripherals can be clocked via an external PLL.

The STM32F302xB/STM32F302xC family operates in the -40 to +85 °C and -40 to +105 °C temperature ranges from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F302xB/STM32F302xC family offers devices in four packages ranging from 48 pins to 100 pins.

The set of included peripherals changes with the device chosen.

3.7.4 Low-power modes

The STM32F302xB/STM32F302xC supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- Sleep mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- Stop mode

  Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

  The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the USB wakeup, the RTC alarm, COMPx, I2Cx or U(S)ARTx.

- Standby mode

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.

  The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin or an RTC alarm occurs.

Note: The RTC, the IWDG and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.8 Interconnect matrix

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU resources thus power supply consumption. In addition, these hardware connections allow fast and predictable latency.

Table 4. STM32F302xB/STM32F302xC peripheral interconnect matrix

Interconnect source	Interconnect destination	Interconnect action
TIMx	TIMx	Timers synchronization or chaining
	ADCx DAC1	Conversion triggers
	DMA	Memory to memory transfer trigger
	Compx	Comparator output blanking
COMPx	TIMx	Timer input: OCREF_CLR input, input capture
ADCx	TIMx	Timer triggered by analog watchdog

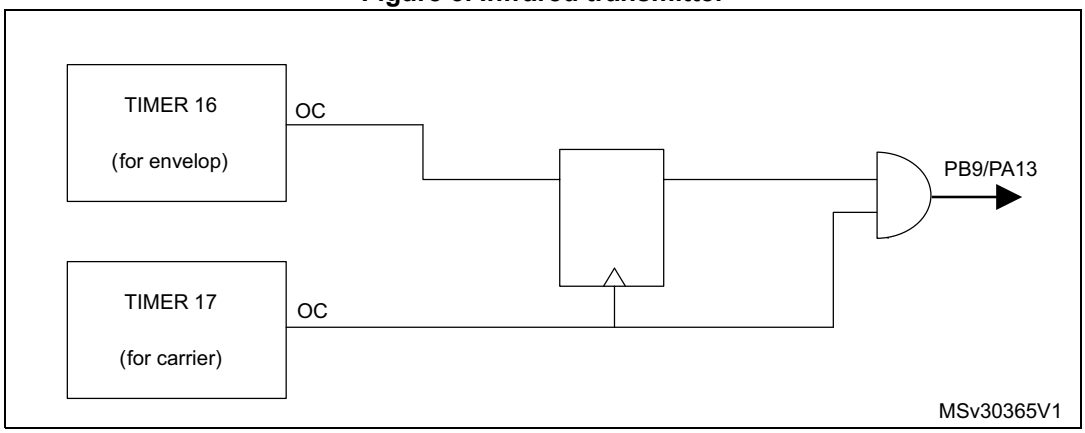
3.25 Infrared Transmitter

The STM32F302xB/STM32F302xC devices provide an infrared transmitter solution. The solution is based on internal connections between TIM16 and TIM17 as shown in the figure below.

TIM17 is used to provide the carrier frequency and TIM16 provides the main signal to be sent. The infrared output signal is available on PB9 or PA13.

To generate the infrared remote control signals, TIM16 channel 1 and TIM17 channel 1 must be properly configured to generate correct waveforms. All standard IR pulse modulation modes can be obtained by programming the two timers output compare channels.

Figure 3. Infrared transmitter



3.26 Touch sensing controller (TSC)

The STM32F302xB/STM32F302xC devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 24 capacitive sensing channels distributed over 8 analog I/O groups.

Capacitive sensing technology is able to detect the presence of a finger near a sensor which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of charging the sensor capacitance and then transferring a part of the accumulated charges into a sampling capacitor until the voltage across this capacitor has reached a specific threshold. To limit the CPU bandwidth usage this acquisition is directly managed by the hardware touch sensing controller and only requires few external components to operate.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Table 10. Capacitive sensing GPIOs available on STM32F302xB/STM32F302xC devices

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
1	TSC_G1_IO1	PA0	5	TSC_G5_IO1	PB3
	TSC_G1_IO2	PA1		TSC_G5_IO2	PB4
	TSC_G1_IO3	PA2		TSC_G5_IO3	PB6
	TSC_G1_IO4	PA3		TSC_G5_IO4	PB7
2	TSC_G2_IO1	PA4	6	TSC_G6_IO1	PB11
	TSC_G2_IO2	PA5		TSC_G6_IO2	PB12
	TSC_G2_IO3	PA6		TSC_G6_IO3	PB13
	TSC_G2_IO4	PA7		TSC_G6_IO4	PB14
3	TSC_G3_IO1	PC5	7	TSC_G7_IO1	PE2
	TSC_G3_IO2	PB0		TSC_G7_IO2	PE3
	TSC_G3_IO3	PB1		TSC_G7_IO3	PE4
	TSC_G3_IO4	PB2		TSC_G7_IO4	PE5
4	TSC_G4_IO1	PA9	8	TSC_G8_IO1	PD12
	TSC_G4_IO2	PA10		TSC_G8_IO2	PD13
	TSC_G4_IO3	PA13		TSC_G8_IO3	PD14
	TSC_G4_IO4	PA14		TSC_G8_IO4	PD15

Table 11. No. of capacitive sensing channels available on STM32F302xB/STM32F302xC devices

Analog I/O group	Number of capacitive sensing channels		
	STM32F302Vx	STM32F302Rx	STM32F302Cx
G1	3	3	3
G2	3	3	3
G3	3	3	2
G4	3	3	3
G5	3	3	3
G6	3	3	3
G7	3	0	0
G8	3	0	0
Number of capacitive sensing channels	24	18	17

Table 19. Alternate functions for port F

Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PF0	-	-	-	I2C2_SDA	-	TIM1_CH3N	-
PF1	-	-	-	I2C2_SCL	-	-	-
PF2	EVENTOUT	-	-	-	-	-	-
PF4	EVENTOUT	COMP1_OUT	-	-	-	-	-
PF6	EVENTOUT	TIM4_CH4	-	I2C2_SCL	-	-	USART3_RTS_DE
PF9	EVENTOUT	-	TIM15_CH1	-	SPI2_SCK	-	-
PF10	EVENTOUT	-	TIM15_CH2	-	SPI2_SCK	-	-

Table 20. STM32F302xB/STM32F302xC memory map, peripheral register boundary addresses

Bus	Boundary address	Size (bytes)	Peripheral
	0x5000 0400 - 0x5000 07FF	1 K	Reserved
AHB3	0x5000 0000 - 0x5000 03FF	1 K	ADC1 - ADC2
	0x4800 1800 - 0x4FFF FFFF	~132 M	Reserved
AHB2	0x4800 1400 - 0x4800 17FF	1 K	GPIOF
	0x4800 1000 - 0x4800 13FF	1 K	GPIOE
	0x4800 0C00 - 0x4800 0FFF	1 K	GPIOD
	0x4800 0800 - 0x4800 0BFF	1 K	GPIOC
	0x4800 0400 - 0x4800 07FF	1 K	GPIOB
	0x4800 0000 - 0x4800 03FF	1 K	GPIOA
	0x4002 4400 - 0x47FF FFFF	~128 M	Reserved
AHB1	0x4002 4000 - 0x4002 43FF	1 K	TSC
	0x4002 3400 - 0x4002 3FFF	3 K	Reserved
	0x4002 3000 - 0x4002 33FF	1 K	CRC
	0x4002 2400 - 0x4002 2FFF	3 K	Reserved
	0x4002 2000 - 0x4002 23FF	1 K	Flash interface
	0x4002 1400 - 0x4002 1FFF	3 K	Reserved
	0x4002 1000 - 0x4002 13FF	1 K	RCC
	0x4002 0800 - 0x4002 0FFF	2 K	Reserved
	0x4002 0400 - 0x4002 07FF	1 K	DMA2
	0x4002 0000 - 0x4002 03FF	1 K	DMA1
	0x4001 8000 - 0x4001 FFFF	32 K	Reserved
APB2	0x4001 4C00 - 0x4001 7FFF	13 K	Reserved
	0x4001 4800 - 0x4001 4BFF	1 K	TIM17
	0x4001 4400 - 0x4001 47FF	1 K	TIM16
	0x4001 4000 - 0x4001 43FF	1 K	TIM15
	0x4001 3C00 - 0x4001 3FFF	1 K	Reserved
	0x4001 3800 - 0x4001 3BFF	1 K	USART1
	0x4001 3400 - 0x4001 37FF	1 K	Reserved
	0x4001 3000 - 0x4001 33FF	1 K	SPI1
	0x4001 2C00 - 0x4001 2FFF	1 K	TIM1
	0x4001 0800 - 0x4001 2BFF	9 K	Reserved
	0x4001 0400 - 0x4001 07FF	1 K	EXTI
	0x4001 0000 - 0x4001 03FF	1 K	SYSCFG + COMP + OPAMP

6.3.4 Embedded reference voltage

The parameters given in *Table 28* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

Table 28. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.2	1.23	1.25	V
		–40 °C < T_A < +85 °C	1.2	1.23	1.24(1)	V
$T_{S\_vrefint}$	ADC sampling time when reading the internal reference voltage	-	2.2	-	-	µs
V_{RERINT}	Internal reference voltage spread over the temperature range	V_{DD} = 3 V ±10 mV	-	-	10(2)	mV
T_{Coeff}	Temperature coefficient	-	-	-	100(2)	ppm/°C

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 29. Internal reference voltage calibration values

Calibration value name	Description	Memory address
V_{REFINT_CAL}	Raw data acquired at temperature of 30 °C V_{DDA}= 3.3 V	0x1FFF F7BA - 0x1FFF F7BB

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.
The current consumption is measured as described in *Figure 12: Current consumption measurement scheme*.
All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz,1 wait state from 24 to 48 MHz and 2 wait states from 48 to 72 MHz)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK2} = f_{HCLK}$ and $f_{PCLK1} = f_{HCLK/2}$
- When f_{HCLK} > 8 MHz, the PLL is ON and the PLL input is equal to HSI/2 (4 MHz) or HSE (8 MHz) in bypass mode.

Table 37. Switching output I/O current consumption

Symbol	Parameter	Conditions[1]	I/O toggling frequency (f_{SW})	Typ	Unit
I_{SW}	I/O current consumption	V_{DD} = 3.3 V C_{ext} = 0 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.90	mA
			4 MHz	0.93	
			8 MHz	1.16	
			18 MHz	1.60	
			36 MHz	2.51	
			48 MHz	2.97	
		V_{DD} = 3.3 V C_{ext} = 10 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.93	
			4 MHz	1.06	
			8 MHz	1.47	
			18 MHz	2.26	
			36 MHz	3.39	
			48 MHz	5.99	
		V_{DD} = 3.3 V C_{ext} = 22 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.03	
			4 MHz	1.30	
			8 MHz	1.79	
			18 MHz	3.01	
			36 MHz	5.99	
		V_{DD} = 3.3 V C_{ext} = 33 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.10	
			4 MHz	1.31	
			8 MHz	2.06	
			18 MHz	3.47	
			36 MHz	8.35	
		V_{DD} = 3.3 V C_{ext} = 47 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.20	
			4 MHz	1.54	
			8 MHz	2.46	
			18 MHz	4.51	
			36 MHz	9.98	

1. CS = 5 pF (estimated value).

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 49*. They are based on the EMS levels and classes defined in the application note AN1709.

Table 49. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25°C, f_{HCLK} = 72 MHz conforms to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25°C, f_{HCLK} = 72 MHz conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 19* and *Figure 20* for standard I/Os.

Figure 19. TC and TTa I/O input characteristics - CMOS port

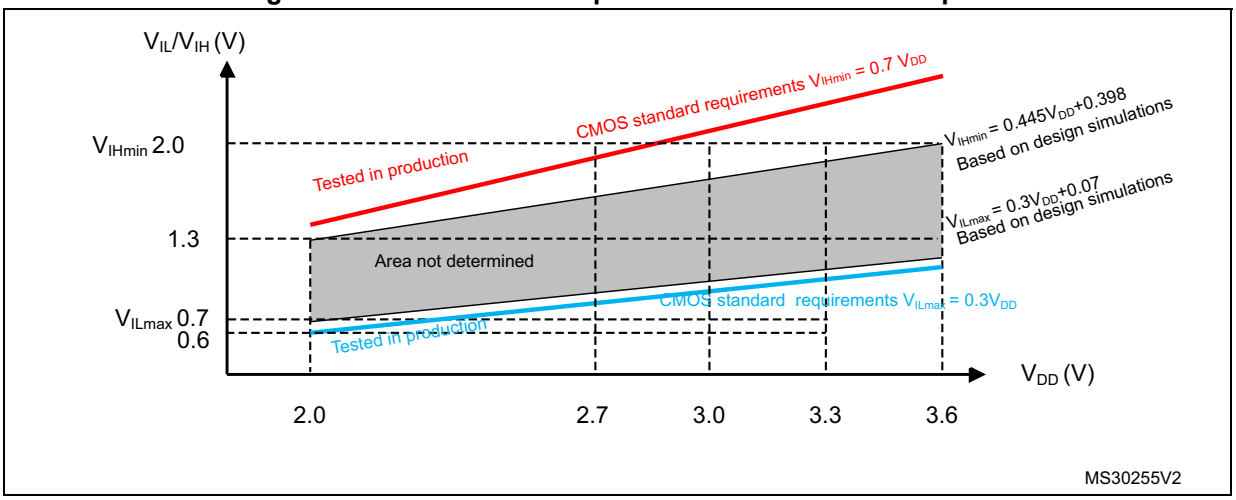
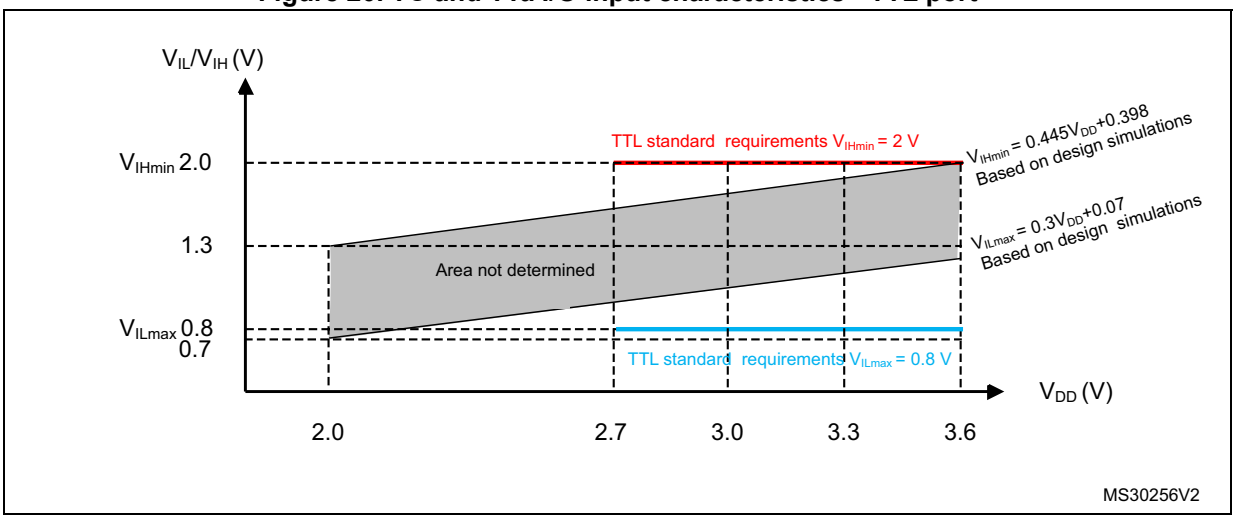


Figure 20. TC and TTa I/O input characteristics - TTL port



SPI/I^2S characteristics

Unless otherwise specified, the parameters given in *Table 63* for SPI or in *Table 64* for I^2S are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 24*.

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I^2S).

Table 63. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode, SPI1 $2.7<V_{DD}<3.6$	-	-	24	MHz
		Slave mode, SPI1 $2.7<V_{DD}<3.6$			24	
		Master mode, SPI1/2/3 $2<V_{DD}<3.6$			18	
		Slave mode, SPI1/2/3 $2<V_{DD}<3.6$			18	
DuCy(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
$t_{su(MI)}$	Data input setup time	Master mode	5.5	-	-	
$t_{su(SI)}$		Slave mode	6.5	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	5	-	-	
$t_{h(SI)}$		Slave mode	5	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	0	-	4*Tpclk	
$t_{dis(SO)}$	Data output disable time	Slave mode	0	-	24	
$t_{v(SO)}$	Data output valid time	Slave mode	-	12	27	
		Slave mode, SPI1 $2.7<V_{DD}<3.6V$	-	12	18	
$t_{v(MO)}$		Master mode	-	1.5	3	
$t_{h(SO)}$	Data output hold time	Slave mode	11	-	-	
$t_{h(MO)}$		Master mode	0	-	-	

1. Guaranteed by characterization results.

Figure 26. SPI timing diagram - slave mode and CPHA = 0

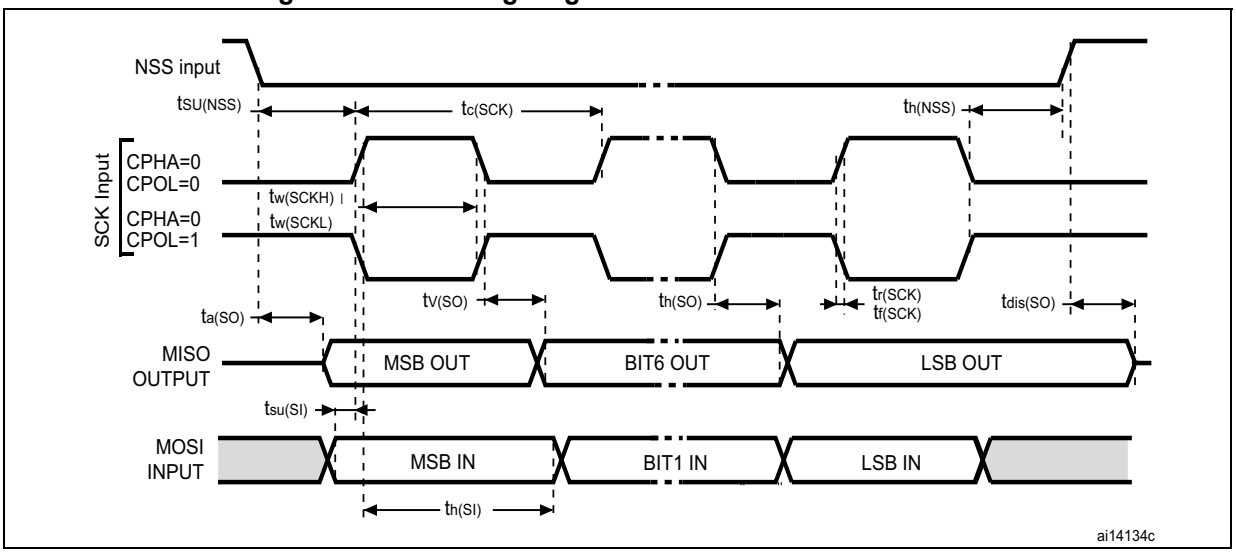
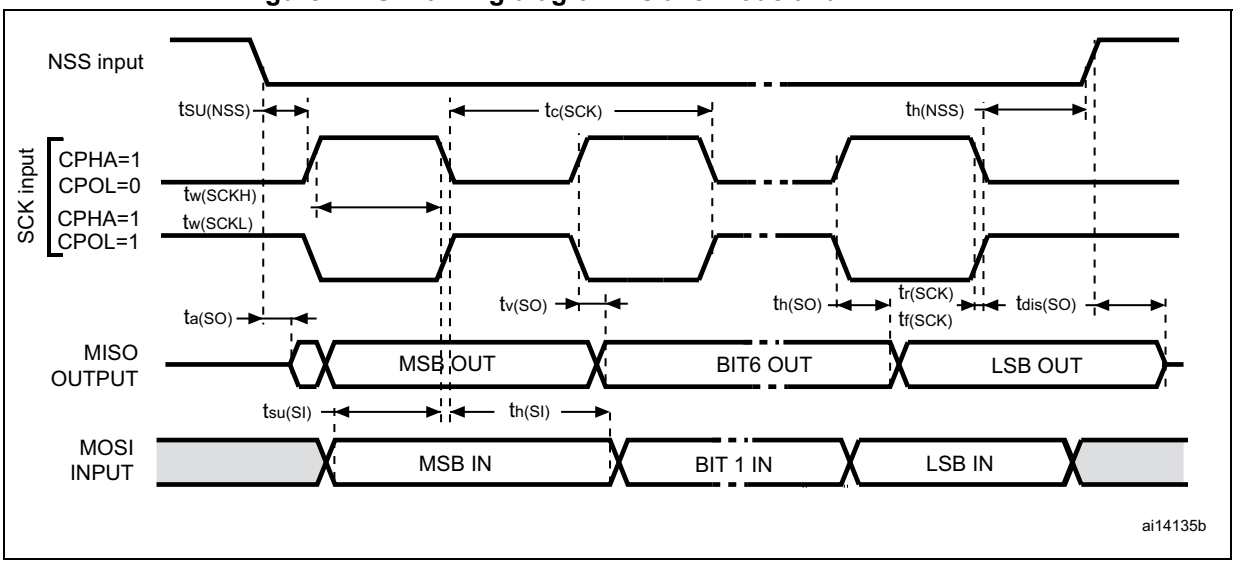


Figure 27. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at $0.5V_{DD}$ and with external C_L = 30 pF.

USB characteristics

Table 65. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB transceiver startup time	1	µs

1. Guaranteed by design.

Table 66. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage(2)	-	3.0(3)	3.6	V
V_{DI}(4)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(4)	Differential common mode range	Includes V_{DI} range	0.8	2.5	
V_{SE}(4)	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(5)	-	0.3	V
V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(5)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F302xB/STM32F302xC USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by design.
5. R_L is the load connected on the USB drivers.

Figure 31. USB timings: definition of data signal rise and fall time

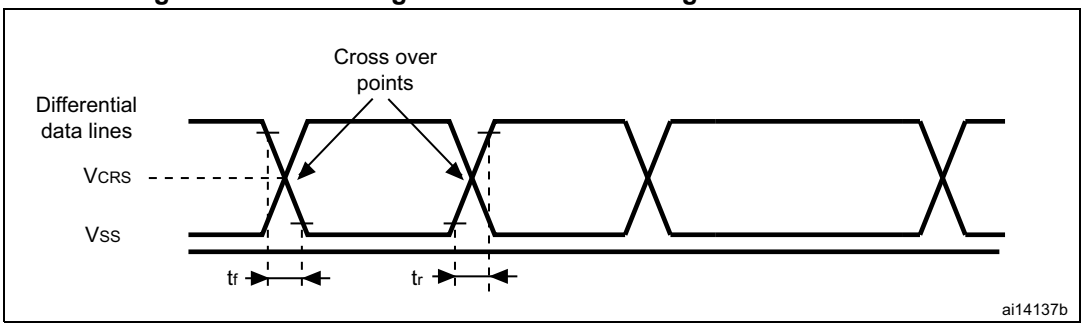


Table 67. USB: Full-speed electrical characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver characteristics						
t_r	Rise time(2)	C_L = 50 pF	4	-	20	ns
t_f	Fall time(2)	C_L = 50 pF	4	-	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	-	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	-	2.0	V
Output driver Impedance(3)	Z_{DRV}	driving high and low	28	40	44	Ω

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).
3. No external termination series resistors are required on USB_DP (D+) and USB_DM (D-), the matching impedance is already included in the embedded driver.

CAN (controller area network) interface

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

Figure 32. ADC typical current consumption on VDDA pin

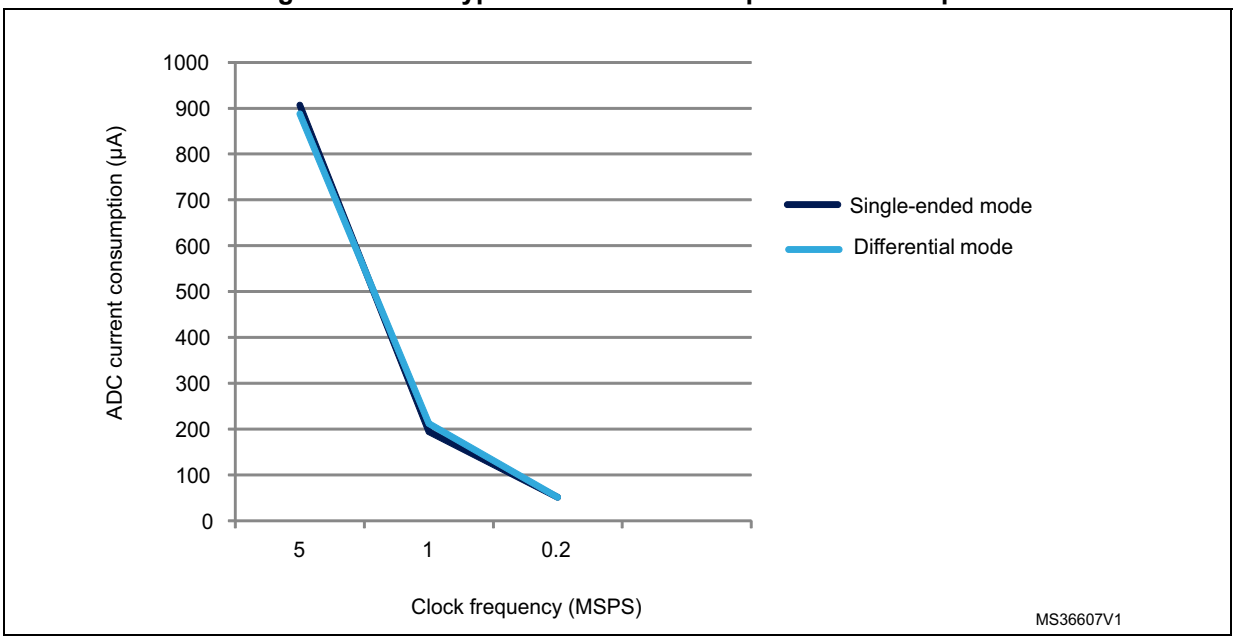


Figure 33. ADC typical current consumption on VREF+ pin

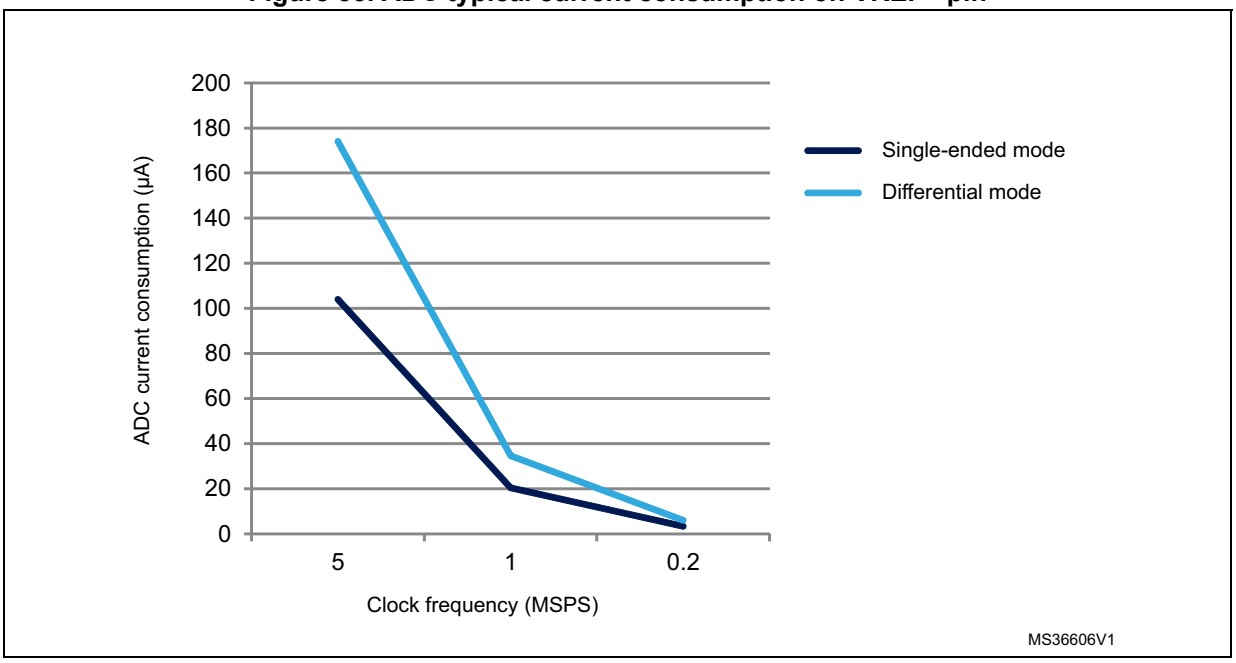


Table 71. ADC accuracy, 100-pin packages(1)(2)(3)

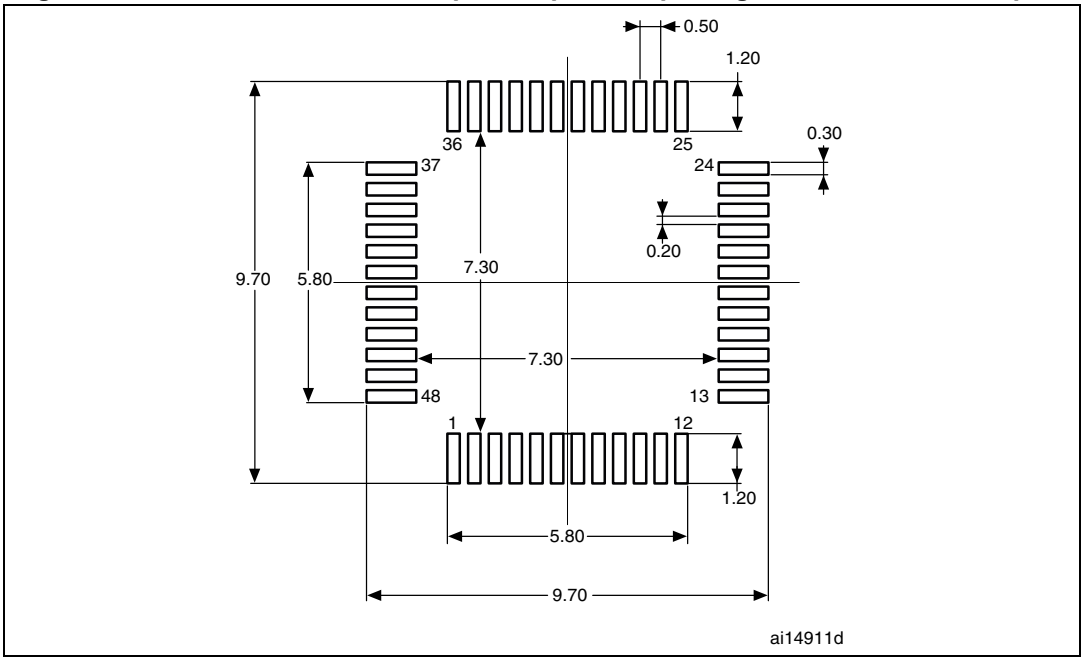
Symbol	Parameter	Conditions			Min (4)	Max(4)	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz, Sampling freq. ≤ 5 Msps 2 V ≤ V_{DDA} , V_{REF+} ≤ 3.6 V 100-pin package	Single Ended	Fast channel 5.1 Ms	-	±6.5	LSB
				Slow channel 4.8 Ms	-	±6.5	
			Differential	Fast channel 5.1 Ms	-	±4	
				Slow channel 4.8 Ms	-	±4	
EO	Offset error		Single Ended	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2	
EG	Gain error		Single Ended	Fast channel 5.1 Ms	-	±6	
				Slow channel 4.8 Ms	-	±6	
			Differential	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
ED	Differential linearity error		Single Ended	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
			Differential	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
EL	Integral linearity error		Single Ended	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2	
ENOB (5)	Effective number of bits		Single Ended	Fast channel 5.1 Ms	10.4	-	bits
				Slow channel 4.8 Ms	10.2	-	
			Differential	Fast channel 5.1 Ms	10.8	-	
				Slow channel 4.8 Ms	10.8	-	

Table 83. LQFP48 – 7 x 7 mm, low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E1	6.80	7.00	7.20	0.2677	0.2756	0.2835
E3	-	5.50	-	-	0.2165	-
e	-	0.50	-	-	0.0197	-
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.08	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 46. LQFP48 - 7 x 7 mm, low-profile quad flat package recommended footprint



1. Dimensions are in millimeters.

9 Revision history

Table 88. Document revision history

Date	Revision	Changes
21-Nov-2013	1	Initial release
16-Apr-2014	2	Updated *Table 38: Peripheral current consumption*. Updated SRAM size in *Table 2: STM32F302xx family device features and peripheral counts*, Cover page and description. Updated *Section 6.3.17: Communications interfaces* I^2C interface. Updated *Table 50: EMI characteristics* conditions :3.3v replaced by 3.6V. Updated *Table 77: Operational amplifier characteristics* adding TS_OPAMP_VOUT row. Updated *Section 3.13: Fast analog-to-digital converter (ADC)*. updated ARM and Cortex trademark. Updated *Table 32: Typical and maximum VDD consumption in Stop and Standby modes* with Max value at 85°C and 105°C. Updated *Table 70: ADC accuracy - limited test conditions, 100-pin packages* and *Table 71: ADC accuracy, 100-pin packages* for 100-pin package. Added *Table 72: ADC accuracy - limited test conditions, 64-pin packages* and *Table 73: ADC accuracy, 64-pin packages*for 64-pin package. Added *Table 74: ADC accuracy at 1MSPS* for 1MSPS sampling frequency. Updated *Table 63: SPI characteristics*. Updated *Table 75: DAC characteristics*. Updated note 2 and note 3 of *Table 69: Maximum ADC RAIN*.
09-Dec-2014	3	Updated core description in cover page. Updated HSI characteristics *Table 44: HSI oscillator characteristics* and *Figure 18: HSI oscillator accuracy characterization results for soldered parts*. Updated *Table 58: TIMx characteristics*. Updated *Table 16: STM32F302xB/STM32F302xC pin definitions* adding note for I/Os featuring an analog output function (DAC_OUT,OPAMP_OUT). Updated *Table 68: ADC characteristics* adding IDDA & IREF consumptions. Added *Figure 32: ADC typical current consumption on VDDA pin* and *Figure 33: ADC typical current consumption on VREF+ pin*. Added *Section 3.8: Interconnect matrix*. Added note after *Table 32: Typical and maximum VDD consumption in Stop and Standby modes*. Updated *Section 7: Package information* with new LQFP100, LQFP64, LQFP48 package marking. Updated *Table 16: STM32F302xB/STM32F302xC pin definitions* and alternate functions tables replacing usart_rts by usart_rts_de.

Table 88. Document revision history (continued)

Date	Revision	Changes
29-Jan-2015	4	Updated cover page with ADC up to 17 channels. Updated *Section 6.3.20: Comparator characteristics* modifying ts_sc characteristics in *Table 76* and adding *Figure 37: Maximum VREFINT scaler startup time from power down*. Updated I_{DD} data in *Table 42: HSE oscillator characteristics*.
17-Apr-2015	5	Updated *Figure 1: STM32F302xB/STM32F302xC block diagram* changing 32 KB of SRAM by 40 KB of SRAM. Updated *Section 7: Package information*: with new package information structure adding 1 sub paragraph for each package. Updated *Figure 41: LQFP100 – 14 x 14 mm, low-profile quad flat package top view example* removing gate mark. Added note for all package device markings: “the following figure gives an example of topside marking orientation versus pin 1 identifier location”. Updated *Table 82: LQFP64 – 10 x 10 mm, low-profile quad flat package mechanical data*. Updated *Table 7: STM32F302xB/STM32F302xC peripheral interconnect matrix* removing TIM8 reference and updating note below the table, replacing by a reference to RM0365.
22-Feb-2016	6	Added WLCSP100: – Updated cover page. – Updated *Table 2: STM32F302xx family device features and peripheral counts*. – Added *Figure 7: STM32F302xB/STM32F302xC WLCSP100 pinout*. – Updated *Table 13: STM32F302xB/STM32F302xC pin definitions*. – Updated *Table 24: General operating conditions*. – Added *Section 7.4: WLCSP100 - 0.4 mm pitch wafer level chip scale package information*. – Updated *Table 86: Package thermal characteristics*. – Updated *Table 87: Ordering information scheme*. Updated *Figure 4*, *Figure 5*, *Figure 6*, *Table 13* and *Table 22* removing all VDD and VSS indexes. Updated all the notes removing ‘not tested in production’. Updated *Table 68: ADC characteristics* adding V_{REF}- negative voltage reference. Updated *Table 21: Voltage characteristics* adding table note 4. Updated *Table 43: LSE oscillator characteristics (fLSE = 32.768 kHz)* LSEDRV[1:0] bits. Updated *Table 28: Embedded internal reference voltage* V_{REFINT} internal reference voltage (min and typ values). Updated *Table 51: ESD absolute maximum ratings* ESD CDM at class 3 and 4 including WLCSP100 package information.